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This article [*J. Micro/Nanolith. MEMS MOEMS* 17(4), 043505 (2018), doi: [10.1117/1.JMM.17.4.043505](https://doi.org/10.1117/1.JMM.17.4.043505)] was originally published online on 3 December 2018 with an error in the caption of Fig. 25. The figure caption appeared incorrectly as “Convergence curves of GA and CMA-ES for optimization of larger and complex mask pattern.” It has been corrected to: “Convergence curves of CMA-ES for optimization of larger and complex mask pattern.”

Also, there was an error in the parameter settings listed in Sec. 3.5. The sentence: “As shown by the purple circle in

Fig. 24, the defect is positioned near a corner of an S-shaped pattern feature, and the defect parameters, x_{pos} , y_{pos} , h_{top} , w_{top} , h_{bot} , and w_{bot} , are set as 50, 65, 9, 27, 8, and 35, respectively” has been corrected to: “As shown by the purple circle in Fig. 24, the defect is positioned near a corner of an S-shaped pattern feature, and the defect parameters, x_{pos} , y_{pos} , h_{top} , w_{top} , h_{bot} , and w_{bot} , are set as 36, 108, 8, 35, 50, 65, respectively.”

All online versions of the article were corrected on 21 February 2019.